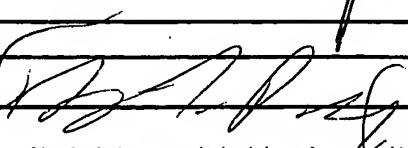


<p>Substitute for Form 1449 A & B/PTO</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(use as many sheets as necessary)</p>				<i>Complete if Known</i>	
				Application Number	Unknown
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				First Named Inventor	Yasunori BITO
				Art Unit	Unknown
				Examiner Name	Unknown
Sheet	1	of	1	Attorney Docket Number	Q78644

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
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FOREIGN PATENT DOCUMENTS						
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.			Translation ⁴
TB		Y. Bito et al., "64% Efficiency Enhancement-Mode Power Heterojunction Fet for 3.5 V Li-ION Battery Operated Personal Digital Cellular Phones", 1998 IEEE MTT-S Int. Microwave Symp-Dig., June 1998, pp. 439-442 with Abstract.			
TB		S. Wada et al., "0.1-μm p ⁺ -GaAs Gate HJFET's Fabricated Using Two-Step Dry-Etching and Selective MOMB Growth Techniques", IEEE Transactions on Electron Devices, Vol. 45, No. 6, June 1998, pp. 1383-1389 with Abstract.			
TB		K. Nishii et al., "High Current/gm Self-Aligned PJ-HFET of Completely Enhancement-Mode Operation", Extended Abstracts of the 1998 International Conference on Solid-State Devices and Materials, 1998, pp. 396-397.			

Examiner Signature		Date Considered	12/11/04
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